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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 10/039,456
Priority Filing Date December 31, 2001
Inventor Ying Huang et al.
Assignee Micron Technology, Inc.
Priority Group Art Unit 2829
Priority Examiner S.B. Geyer
Attorney's Docket No. MI22-2347
Title: An Improved Method, Structure and Process Flow to Reduce Line-Line Capacitance
with Low-K Material

INFORMATION DISCLOSURE STATEMENT

References -- See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 10/039,456, filed December 31, 2001, upon which the above-identified application relies for a priority date under 35 U.S.C. §120. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Date: 7-23-03


D. Brent Kenady
Reg. No. 40,045

Form PTO-1449				U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2347		Priority SERIAL NO. 10/039,456	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Ying Huang et al.					
				FILING DATE		GROUP			
U.S. PATENT DOCUMENTS									
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
	AA	5,946,601	8/99	Wong et al.					
	AB	6,033,979	3/00	Endo					
	AC	6,037,664	3/00	Zhao et al.					
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	AI	6,410,437 B1	06/25/02	Flanner et al.					
	AJ								
	AK								
	AL								
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country		Class	Subclass	Translation	
								Yes	No
	AM								
	AN								
	AO								
	AP								
	AQ								
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
	AR		Baliga, John, "Options for CVD of Dielectrics Include Low-k Materials," Semiconductor International June 1998, pp. 1-6						
	AS		Singer, Peter, "Dual-Damascene Challenges Dielectric-Etch," Semiconductor International August 1999, pp. 1-5						
	AT								
EXAMINER				DATE CONSIDERED					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>									